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Technical Sessions (Oral Sessions)

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Dense, Conformal APF Amorphous Carbon Film for SiC Power Device Processing and Integration...N/A Yi Zheng*, Ricky Fang, Ludovico Megalini, Fengshou Wang, Joseph Lee, Dustin Ho, Jang Seok Oh, Bryan Turner, David Britz, Durga Chaturvedula and Zheng Yuan (Applied Materials, USA)

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Myeong-Cheol Shin and Sang-Mo Koo (Kwangwoon University, Korea)

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Aug. 29, Tuesday

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Chair: Prof. Hui-Hsin Hsiao (National Taiwan University)

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Ballroom A

Chair: Prof. Po-Hung Chen (National Yang Ming Chiao Tung University) Co-Chair: Prof. Alberto Castellazzia (Kyoto University of Advanced Science)

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